

Cold UHV pipe for the GBAR antiproton trap

Seoul National University

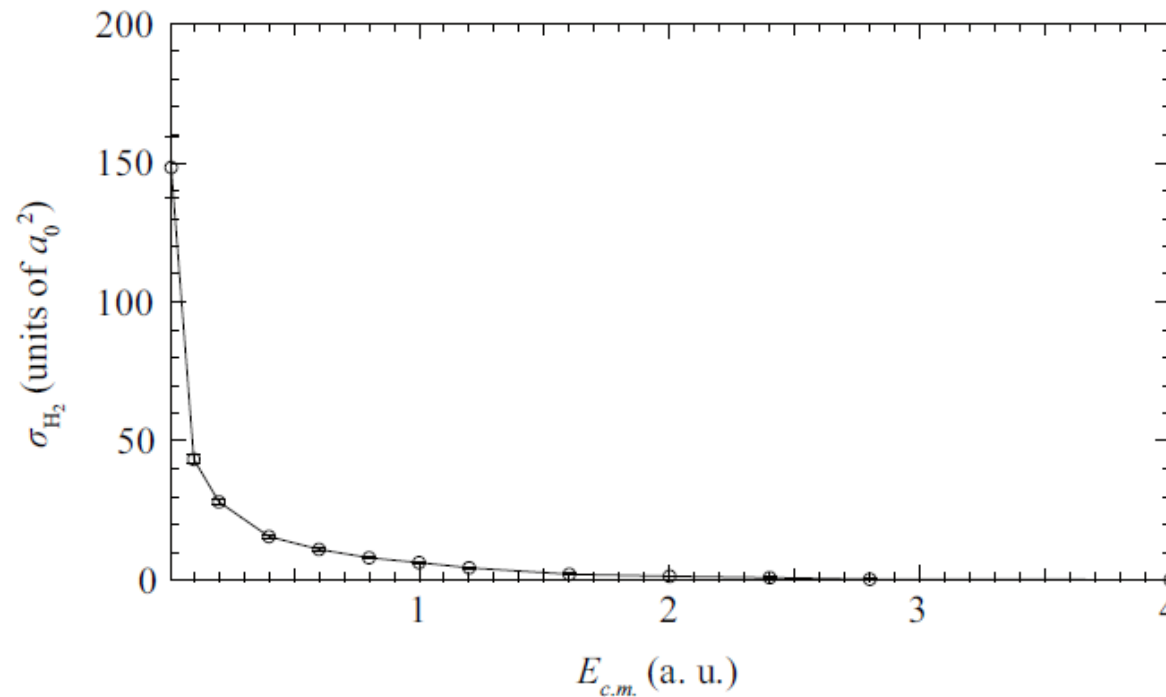
07.Dec.2018

- Why UHV is needed
- Reference Research
- Multi-Ring Electrodes(MRE)
- Cold UHV pipe for the GBAR antiproton trap drawing
- UHV pipe cooling system & Heat Loading
- Vacuum Test in room temperature
- Vacuum Control System

Why UHV is needed

Collision frequency : $\nu_{H_2} = \sigma_{H_2} v n (/s)$

Cross section of hydrogen molecule and antiproton :



$$a_0^2 = 2.5 \times 10^{-21} (m^2)$$

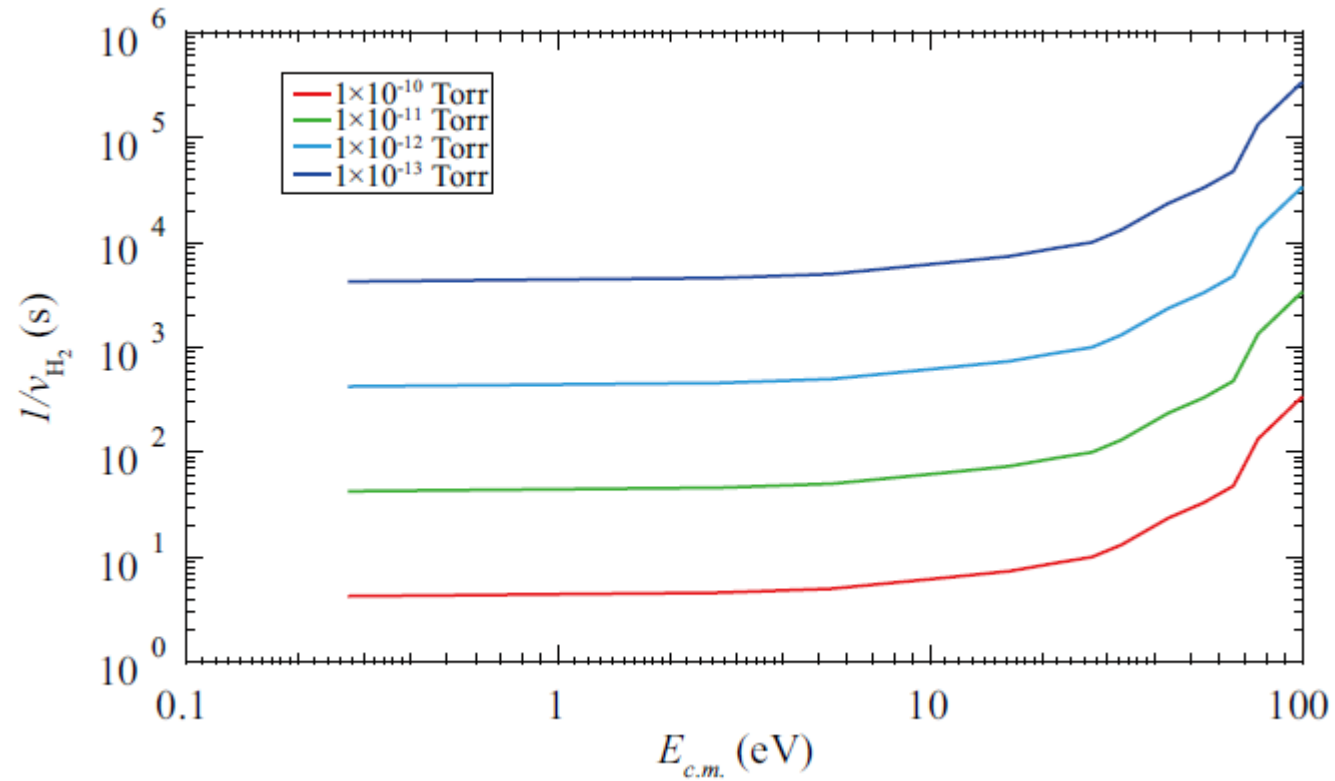
$$\text{a. u.} = 931.494 (MeV/c^2)$$

J.S. Cohen. Molecular effects on antiproton capture by H_2 and the states of $p\bar{p}$ formed.

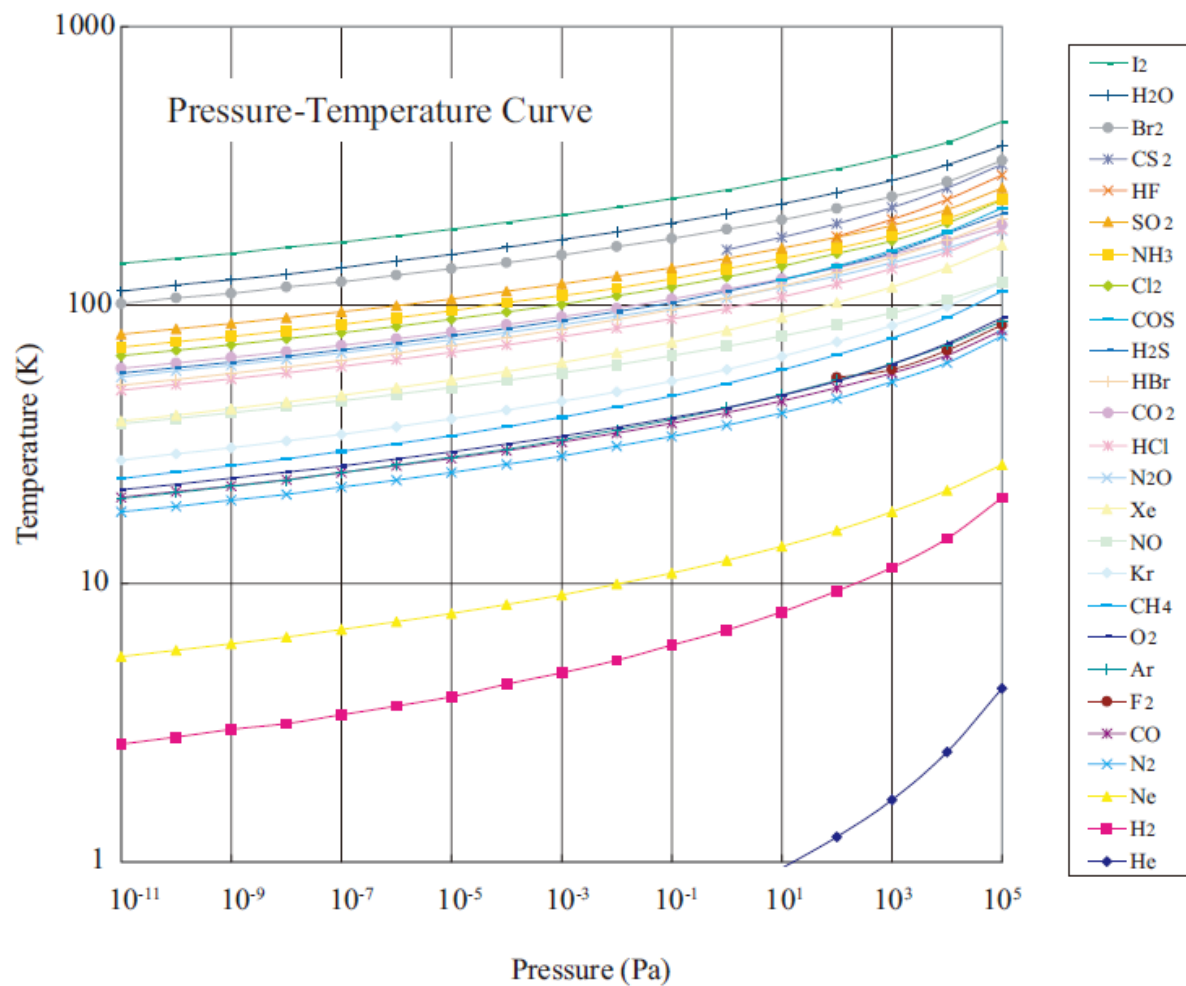
Physical Review A, 56(5):3583, 1997.

Number density of the hydrogen molecules : $n = N/V = P/kT$

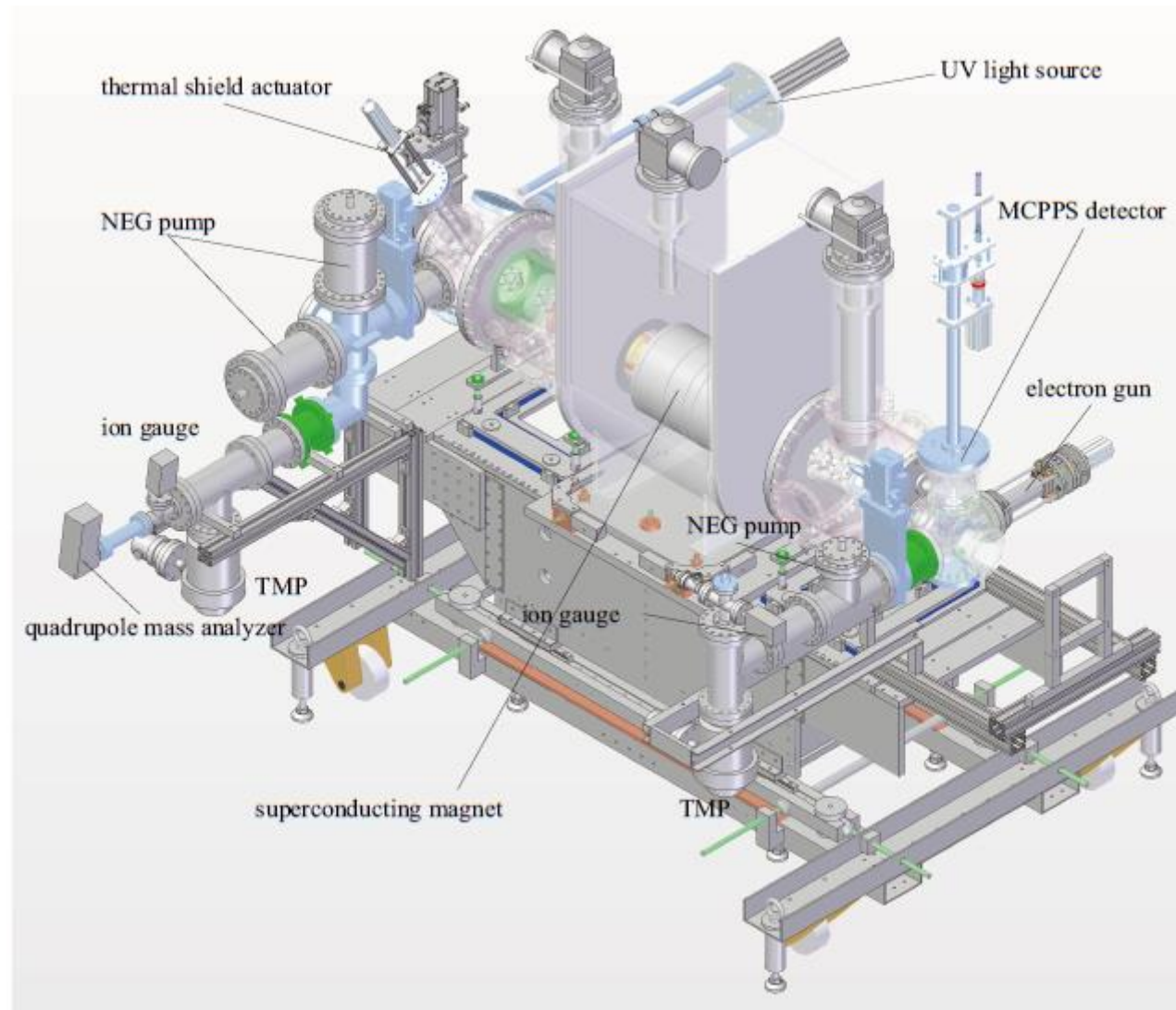
Mean free time($1/v_{H_2}$) of antiproton for several different hydrogen pressures



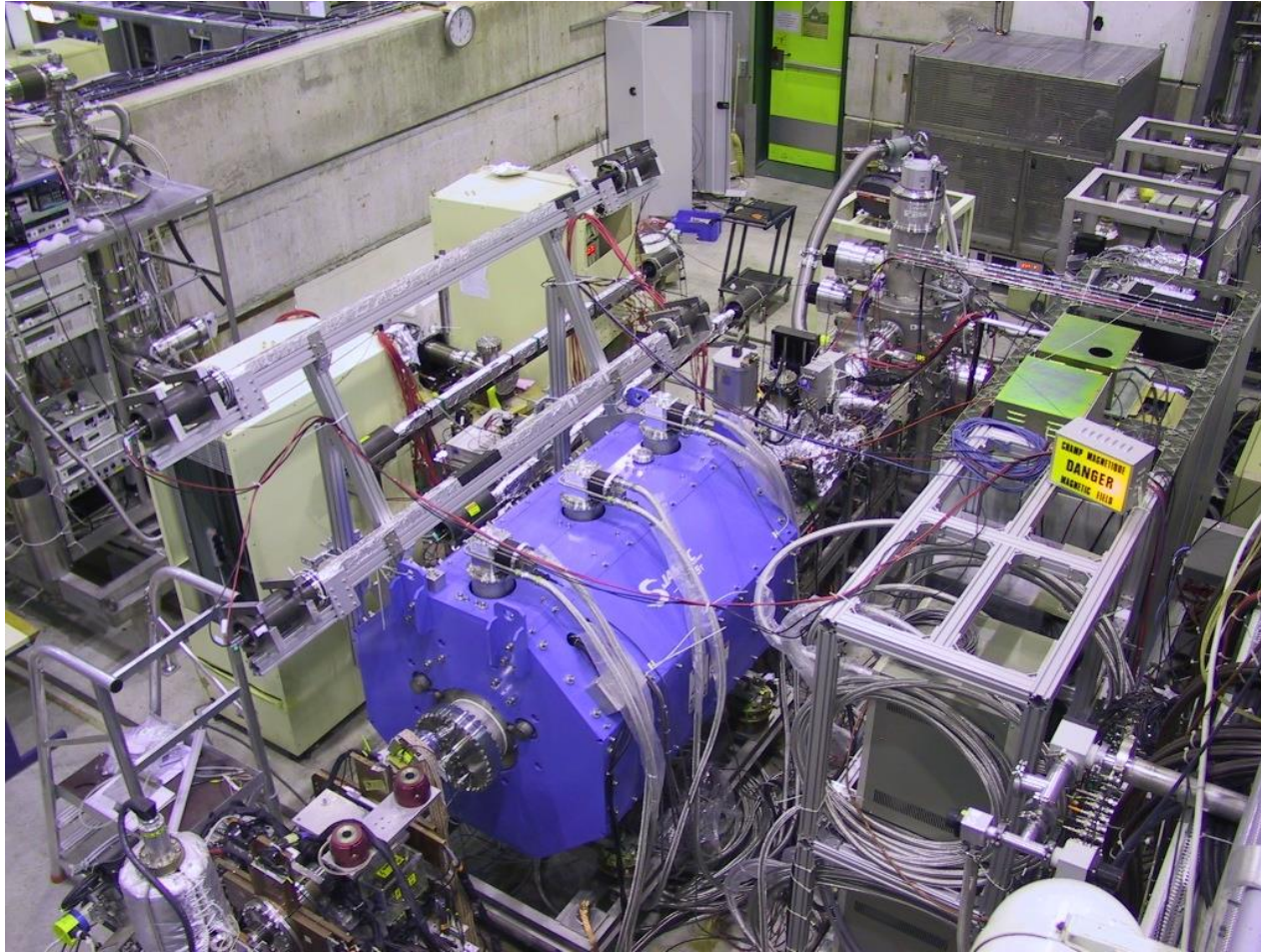
The vapor pressure of most of the gases can be reduced by cooling the apparatus down to about 10K



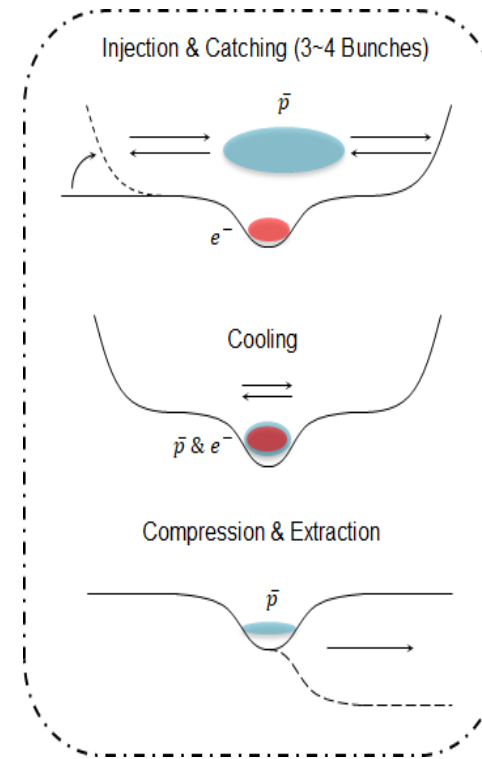
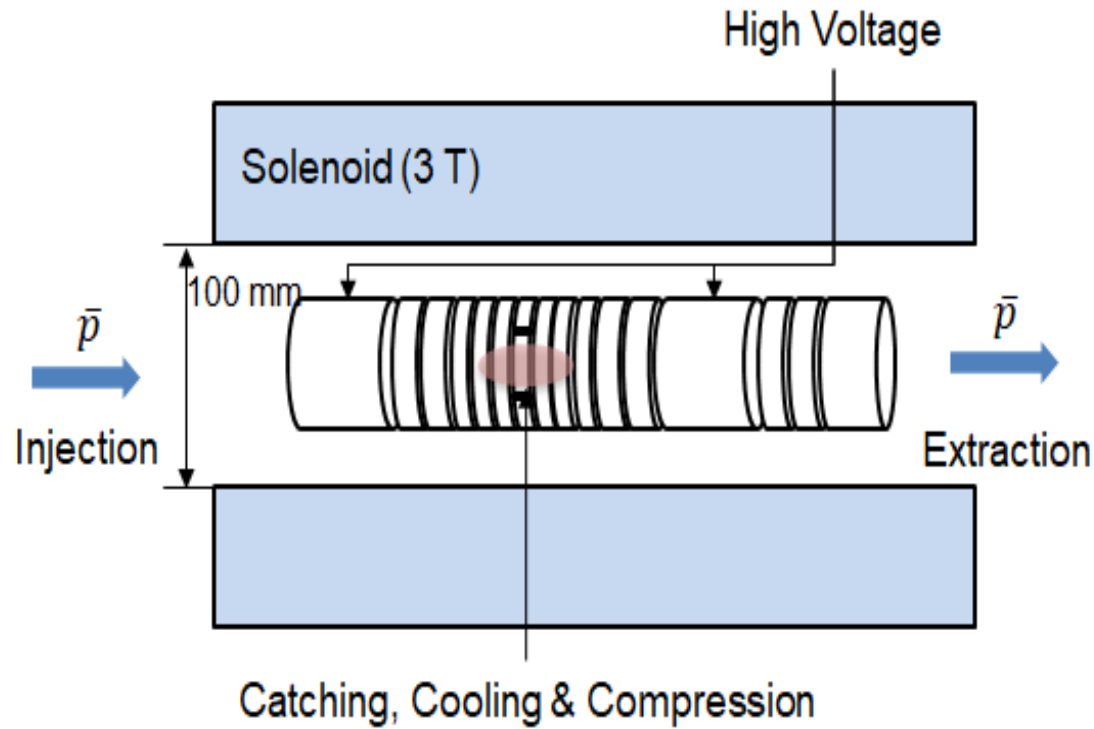
Reference Research 1 - Cusp Trap



Reference Research 2 - Musashi Trap

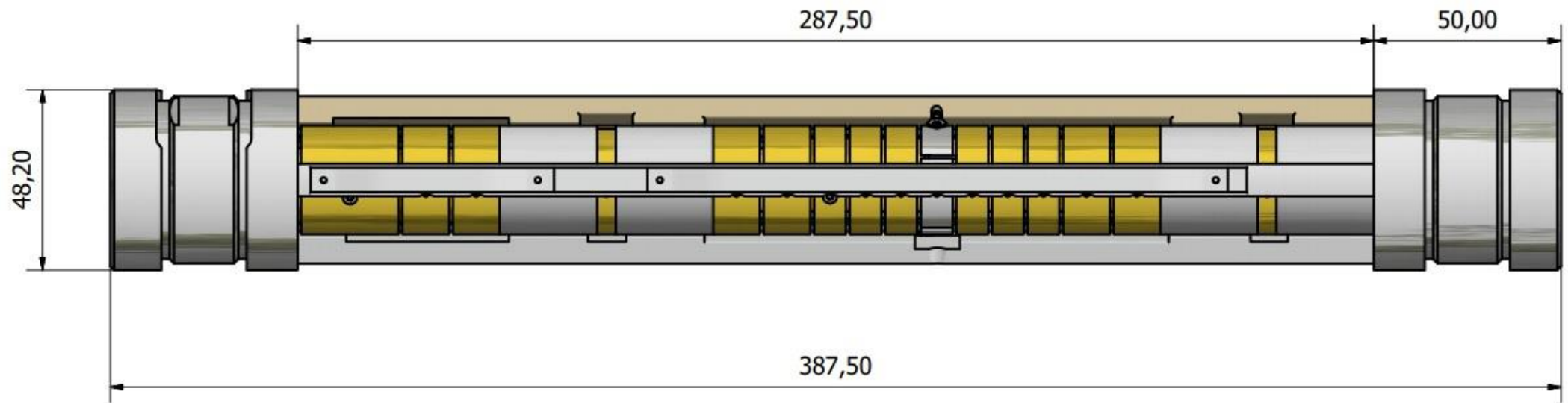
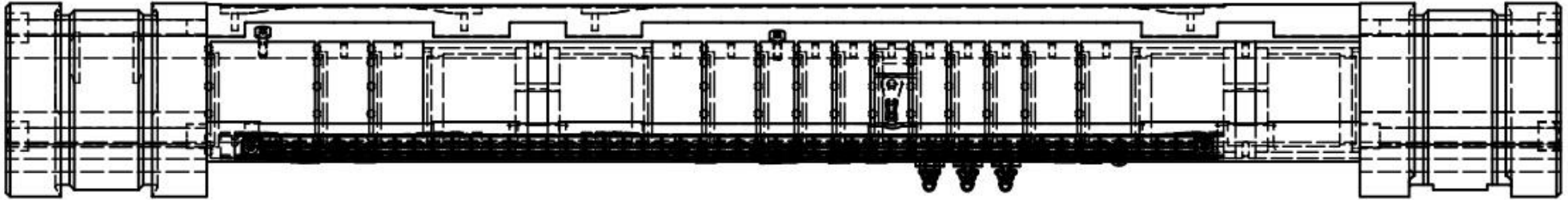


Multi-Ring Electrodes

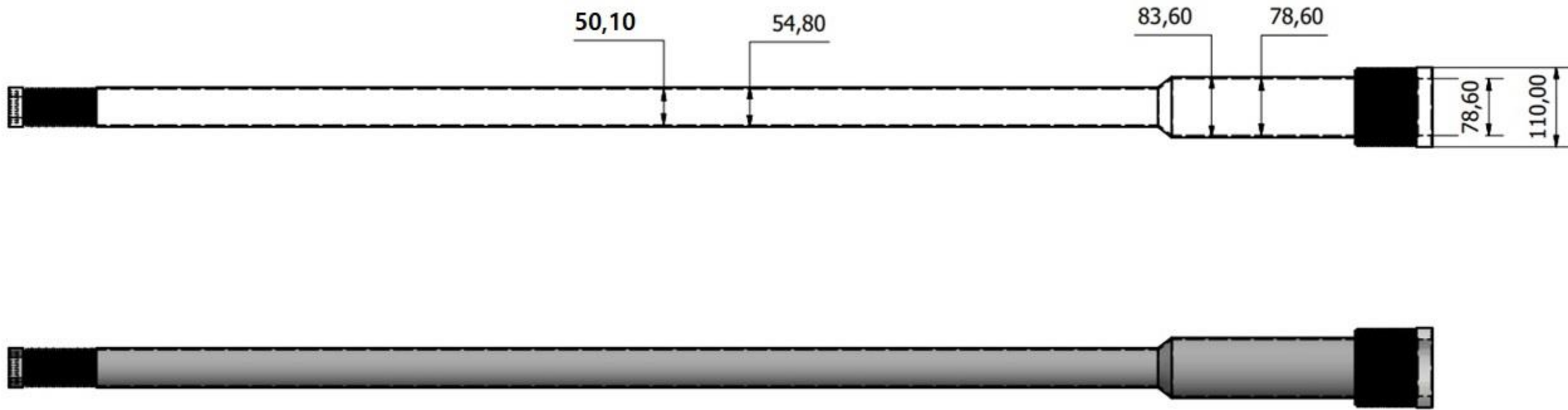


To make a large number of antihydrogen atom efficiently, trapping and cooling of antiproton beam before the reaction is important. A penning trap composed of high field superconducting solenoid and multi-ring electrodes(MRE) to form a harmonic electric potential is designed.

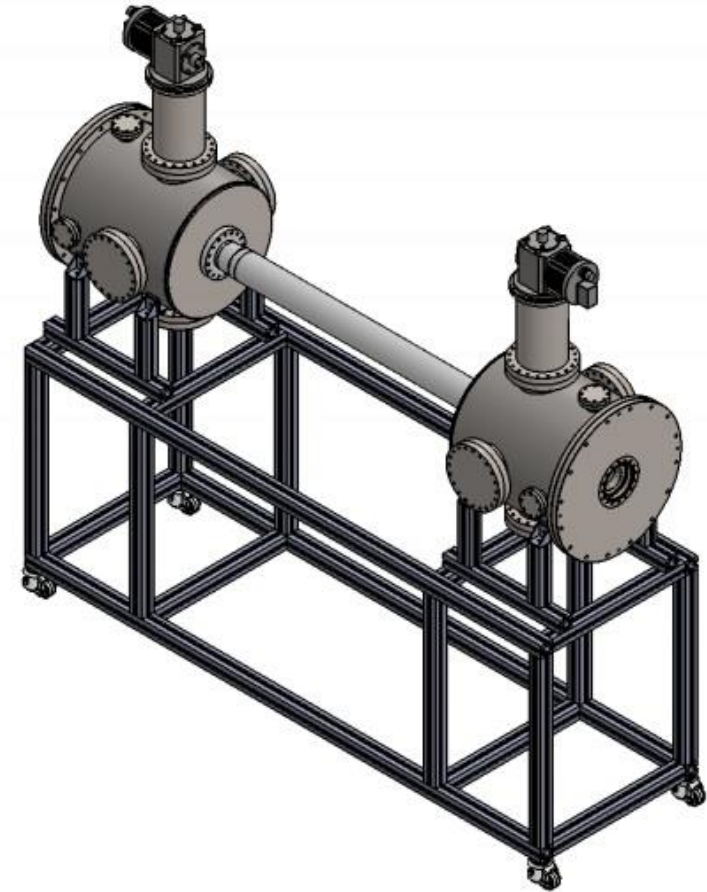
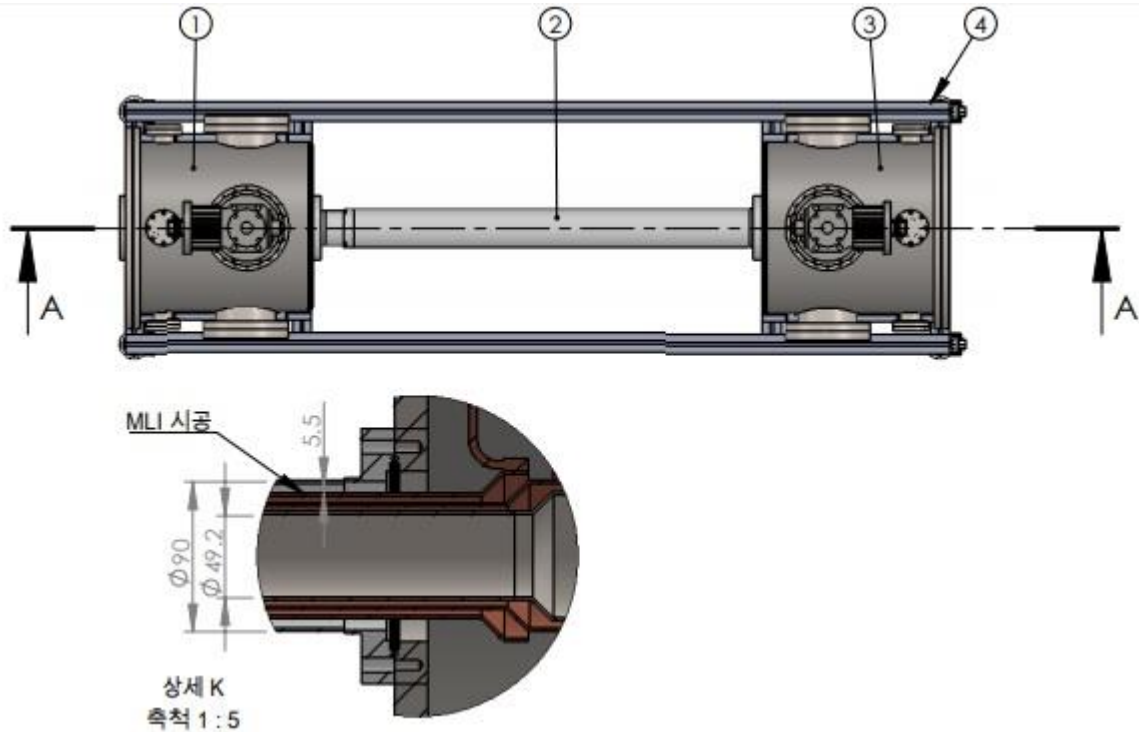
Multi-Ring Electrodes



Cold UHV pipe for the GBAR antiproton trap drawing



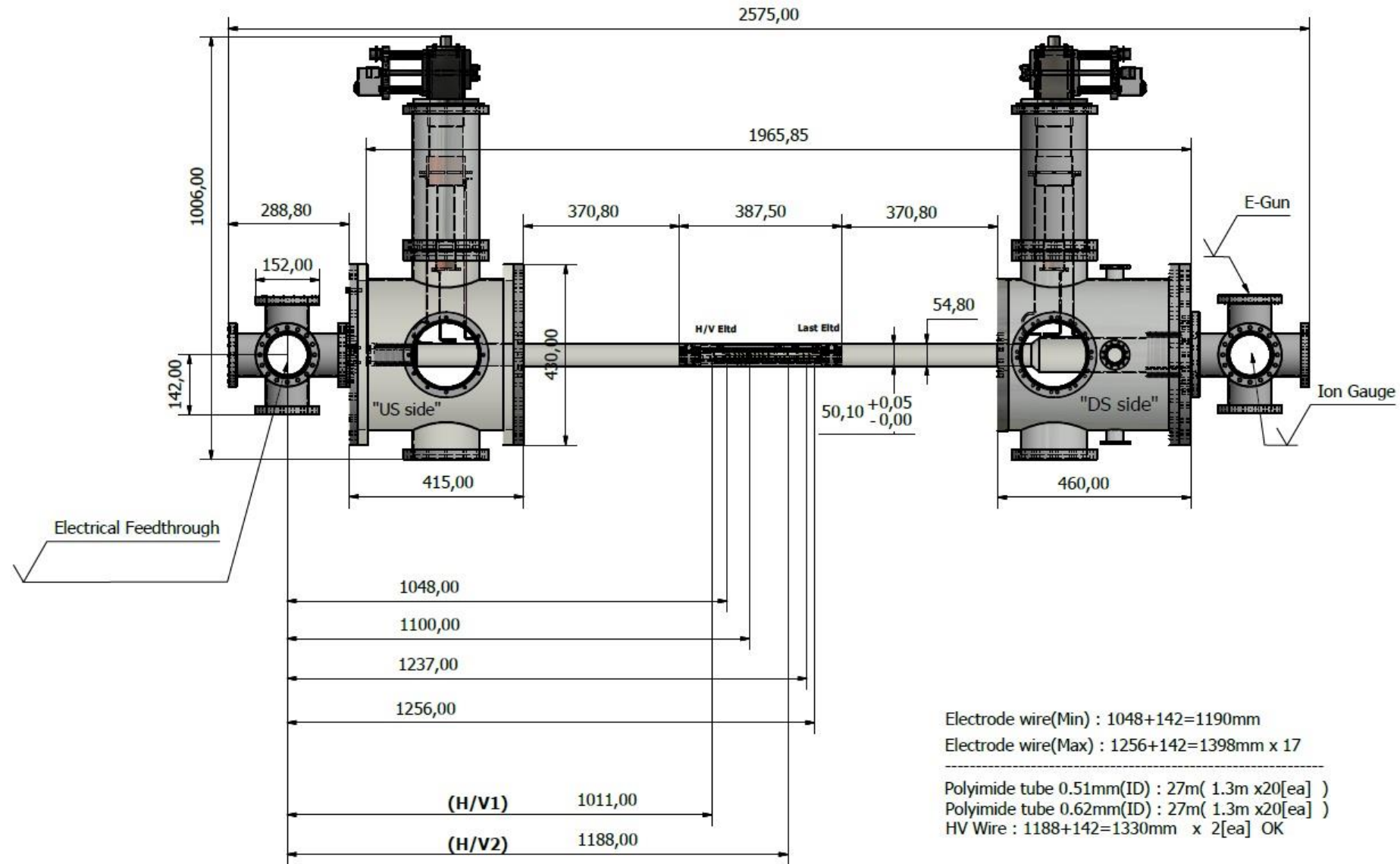
Cold UHV pipe for the GBAR antiproton trap drawing



In order to cool down antiproton beam, and make ultra-high vacuum lower than 10^{-12} Torr, temperature under 10K is needed. So, Cold UHV chamber at 4.2K temperature is designed.

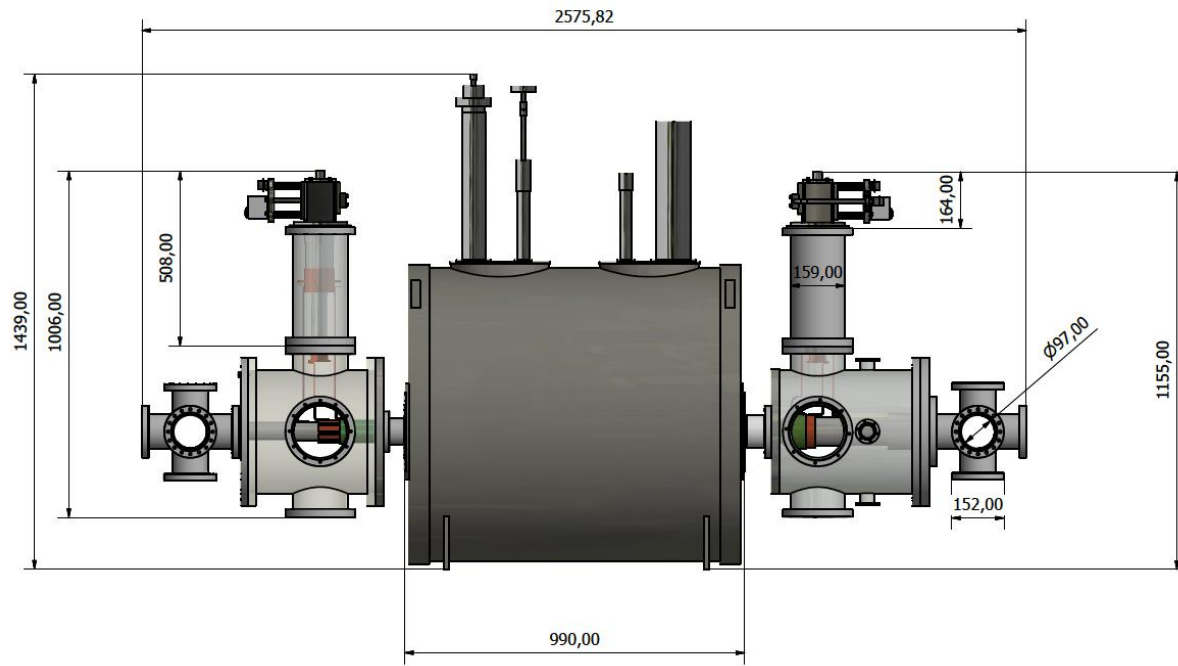
MRE is in the UHV bore tube, whose length is 1944mm. Cryocooler is installed both side of UHV bore tube, and OVC(outer vacuum chamber) is outside of the bore tube and cryocooler.

Cold UHV pipe for the GBAR antiproton trap drawing

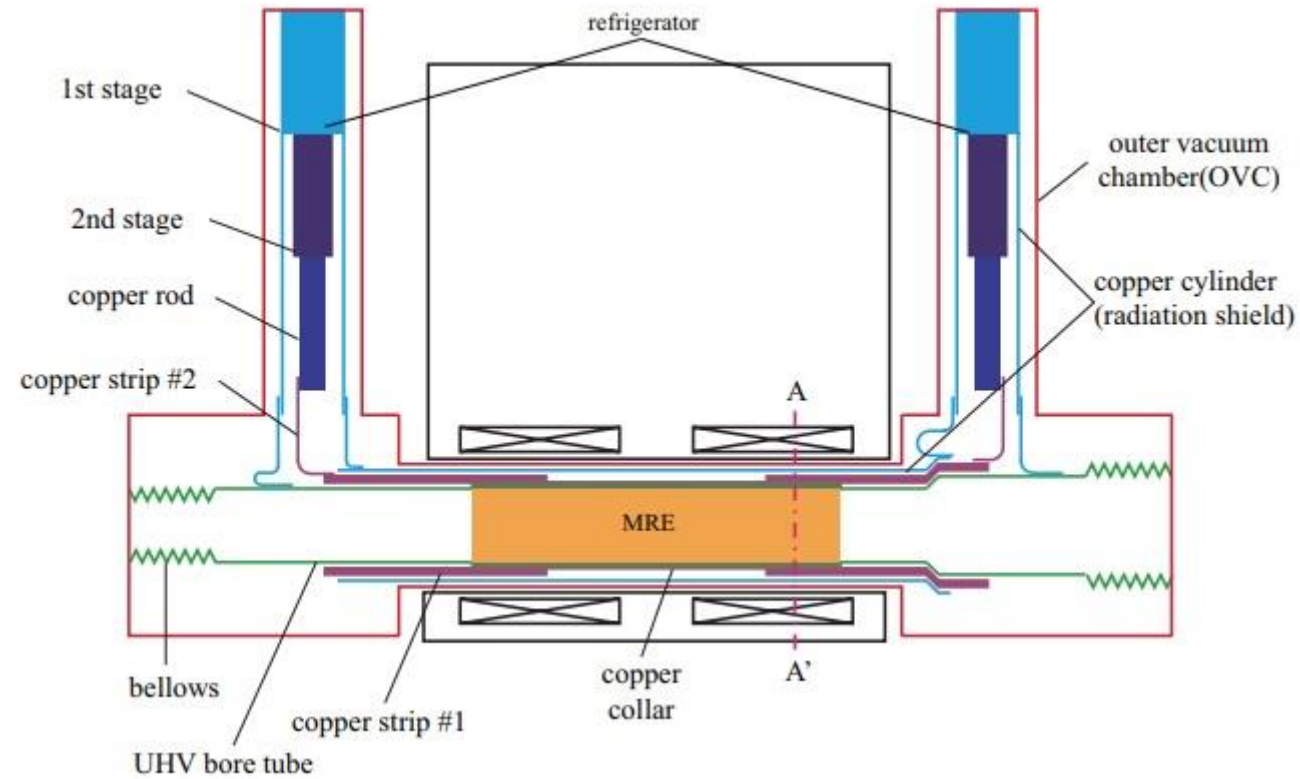


A Trap view

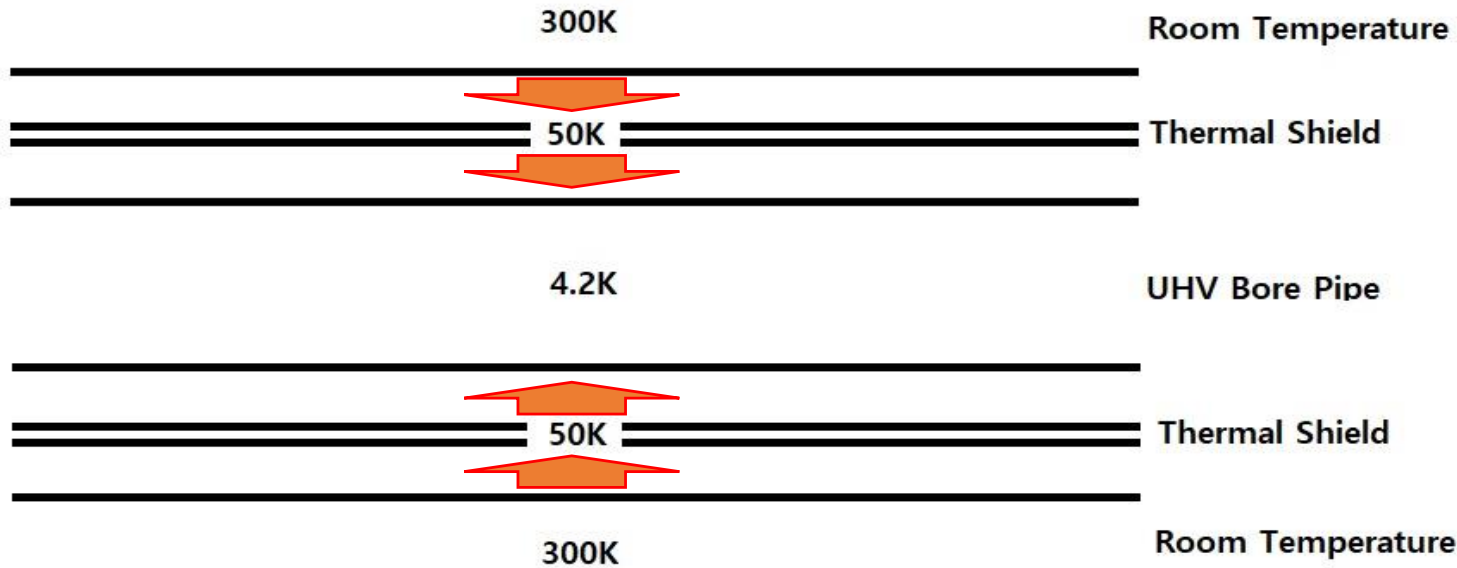
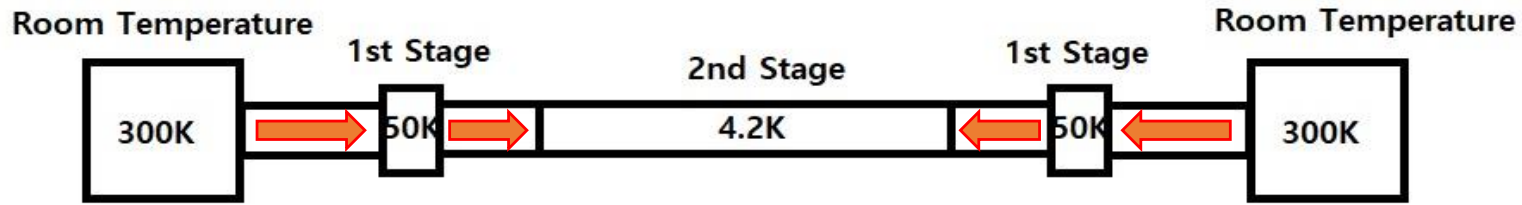
Cold UHV pipe for the GBAR antiproton trap drawing



Schematic Drawing of the UHV pipe cooling system



Heat Loading and Radiation



$$Q_{Heat Load} = \frac{kA(T_H - T_C)}{L_t}$$

$$Q_{H_{300K_{50K}}} = 0.894$$

$$Q_{H_{50K_{4.2K}}} = 0.817$$

$$Q_{Radiation} = \sigma * A * E * (T_H^4 - T_C^4)$$

$$E_{300K_{50K}} = \frac{1}{\frac{1}{\epsilon_2} + \frac{A_2}{A_1} \left(\frac{1}{\epsilon_1} - 1 \right)} = 0.109$$

$$Q_{R_{300K_{50K}}} =$$

$$(5.67 \times 10^{-8}) * (0.31) * (0.109) * (300^4 - 50^4)$$

$$= 15.514$$

$$E_{50K_{4.2K}} = \frac{1}{\frac{1}{\epsilon_2} + \frac{A_2}{A_1} \left(\frac{1}{\epsilon_1} - 1 \right)} = 0.1884$$

$$Q_{50K} =$$

$$(5.67 \times 10^{-8}) * (0.26) * (0.1884) * (50^4 - 4.2^4)$$

$$= 0.017$$

Radiation

Shield 복사열침입량 계산

$$Q = \sigma \cdot A \cdot E \cdot (T_h^4 - T_c^4)$$

온도조건	구분	수치
50K shield Vessel	Outer Dismeter	78 mm
	Inner Diameter	74 mm
	Length	1230 mm
	Temperature (Tc)	50 K
	material	Cu
	emissivity (ϵ_c)	0.3
Vacuum Vessel	Outer Dismeter	93 mm
	Inner Diameter	89 mm
	Length	1230 mm
	Temperature (Th)	300 K
	material	SUS316L
	emissivity (ϵ_h)	0.13
원주율	π	3.1416
스테판-볼츠만 상수	σ	$5.67E-08 \text{ W/m}^2 \cdot \text{K}^4$
Shield Vessel 표면적	옆	0.30 m ²
	상하	0.01 m ²
	전체 (A)	0.31 m ²
Vacuum Vessel 표면적	옆	0.34 m ²
	상하	0.01 m ²
	전체	0.36 m ²
실효방사율	E	$1.09E-01$
단열재 효과		0.2
복사열전달량	Q옆 (ϵ_h 로 계산)	17.981 W
	Q상하 (ϵ_h 로 계산)	0.570 W
	Q전체 (ϵ_h 로 계산)	18.552 W
	Q옆 (E로 계산)	15.037 W
	Q상하 (E로 계산)	0.477 W
	Q전체 (E로 계산)	15.514 W
복사열전달량 단열재 효과 반영	Q옆 (ϵ_h 로 계산)	3.596 W
	Q상하 (ϵ_h 로 계산)	0.114 W
	Q전체 (ϵ_h 로 계산)	3.710 W
	Q옆 (E로 계산)	3.007 W
	Q상하 (E로 계산)	0.095 W
	Q전체 (E로 계산)	3.103 W

Radiation

헬륨조 복사열침입량 계산

$$Q = \sigma \cdot A \cdot E \cdot (T_h^4 - T_c^4)$$

온도조건	구분	수치
Bore Pipe	Outer Dismeter	66 mm
	Inner Diameter	62 mm
	Length	1230 mm
	Temperature (Tc)	4.2 K
	material	Cu
	emissivity (ϵ_c)	0.3
50K Shield	Outer Dismeter	78 mm
	Inner Diameter	74 mm
	Length	1230 mm
	Temperature (Th)	50 K
	material	Cu
	emissivity (ϵ_h)	0.3
원주율	π	3.1416
스테판-볼츠만 상수	σ	$5.67E-08 \text{ W/m}^2 \cdot \text{K}^4$
Lhe Vessel 표면적	옆	0.26 m2
	상하	0.01 m2
	전체 (A)	0.26 m2
Shield Vessel 표면적	옆	0.30 m2
	상하	0.01 m2
	전체	0.31 m2
실효방사율	E	$1.884E-01$
단열재 효과		0.2
복사열전달량	Q옆 (ϵ_h 로 계산)	0.027 W
	Q상하 (ϵ_h 로 계산)	0.001 W
	Q전체 (ϵ_h 로 계산)	0.028 W
	Q옆 (E로 계산)	0.017 W
	Q상하 (E로 계산)	0.000 W
	Q전체 (E로 계산)	0.017 W
복사열전달량 단열재 효과 반영	Q옆 (ϵ_h 로 계산)	0.005 W
	Q상하 (ϵ_h 로 계산)	0.000 W
	Q전체 (ϵ_h 로 계산)	0.006 W
	Q옆 (E로 계산)	0.003 W
	Q상하 (E로 계산)	0.000 W
	Q전체 (E로 계산)	0.003 W

Heat Loading

구분			온도(K)			열전도율(W/m.K)	Pipe 외경(m)	두께(m)	면적(m2)	전체길이(m)	열부하(W)	수량	총 열부하(W)	비고
						k	OD	t	A	Lt	Q		Qt	
50K Thermal shield	전도	Left 측	300	-	50	9.76	0.0532	0.00015	2.49992E-05	0.2	0.304991	1	0.305	
		Right 측	300	-	50	9.76	0.077	0.0002	4.82549E-05	0.2	0.588709	1	0.589	
	합계(전도)												0.894	
	복사	표면적	300	-	50								15.514	단열재 효과 무시
		합계(복사)												15.514
합계(Total)													16.408	

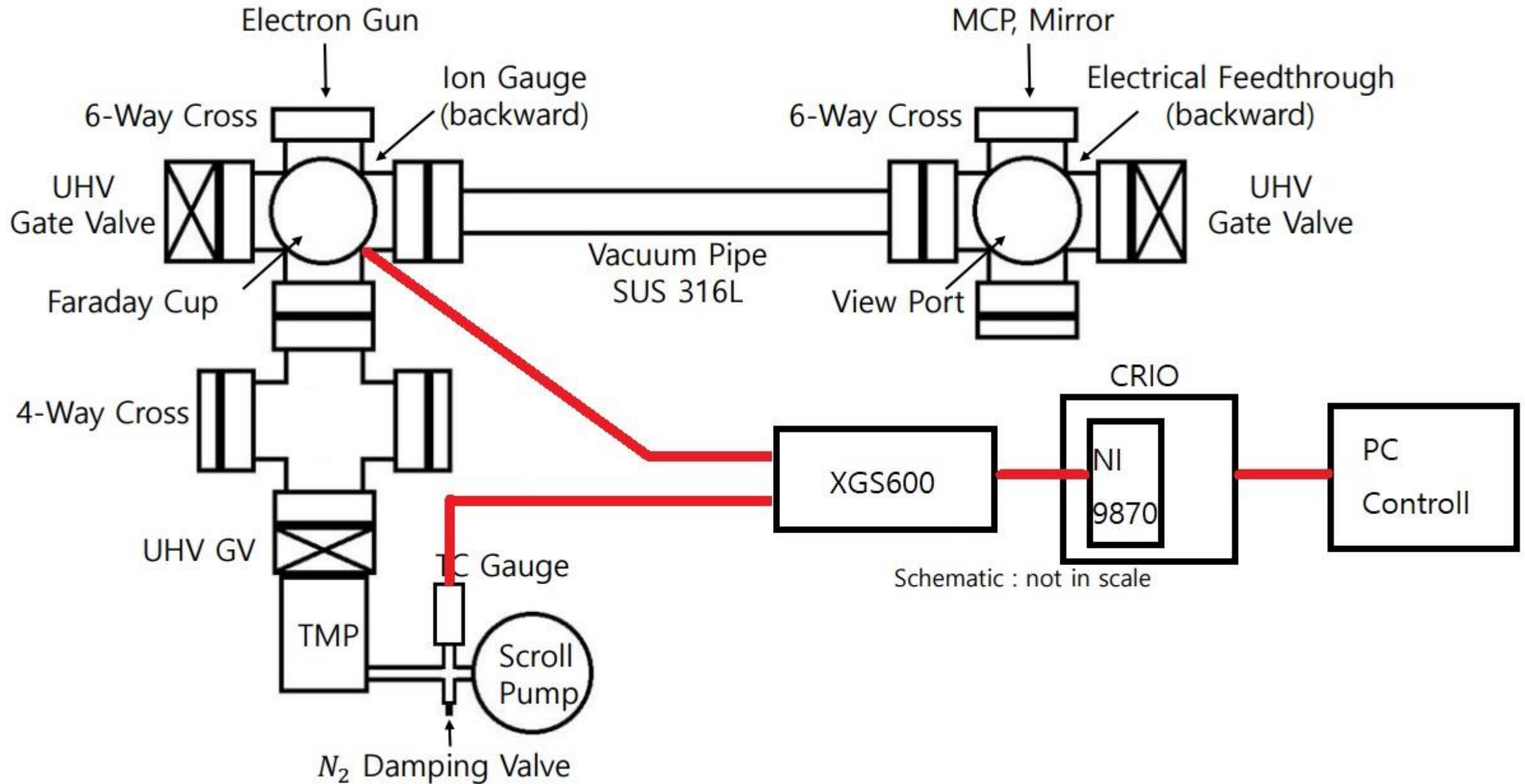
구분			온도(K)			열전도율(W/m.K)	Pipe 외경(m)	두께(m)	면적(m2)	전체길이(m)	열부하(W)	수량	총 열부하(W)	비고
						k	OD	t	A	Lt	Q		Qt	
4.2K	전도	Left 측	50	-	4.2	3.24	0.0532	0.002	0.000321699	0.144	0.331511	1	0.332	
		Right 측	50	-	4.2	3.24	0.077	0.002	0.000471239	0.144	0.485612	1	0.486	
	합계(전도)												0.817	
	복사	표면적	50	-	4.2								0.017	단열재 효과 무시
		합계(복사)												0.017
합계(Total)													0.835	

Sumitomo Cryocooler : RDK-415D		2대 적용
Cooling power@4.2K	1.5W	3 W
Cooling power@30K	15W	30 W

Cooling Power @ 4.2K 0.835W < 3W : Enough

Cooling Power @ 30K 16.408W < 30W : Enough

Vacuum Test in Room Temperature

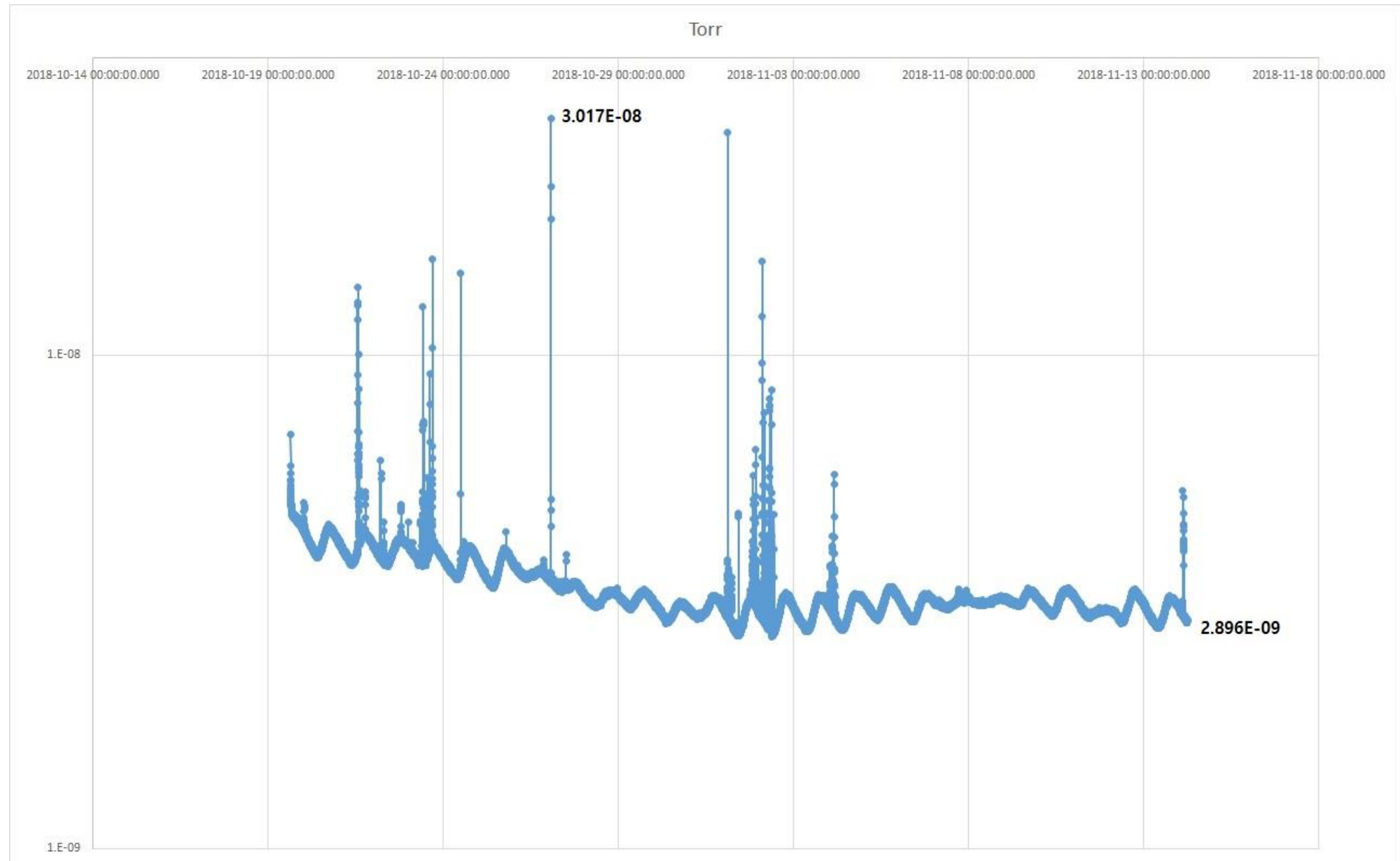




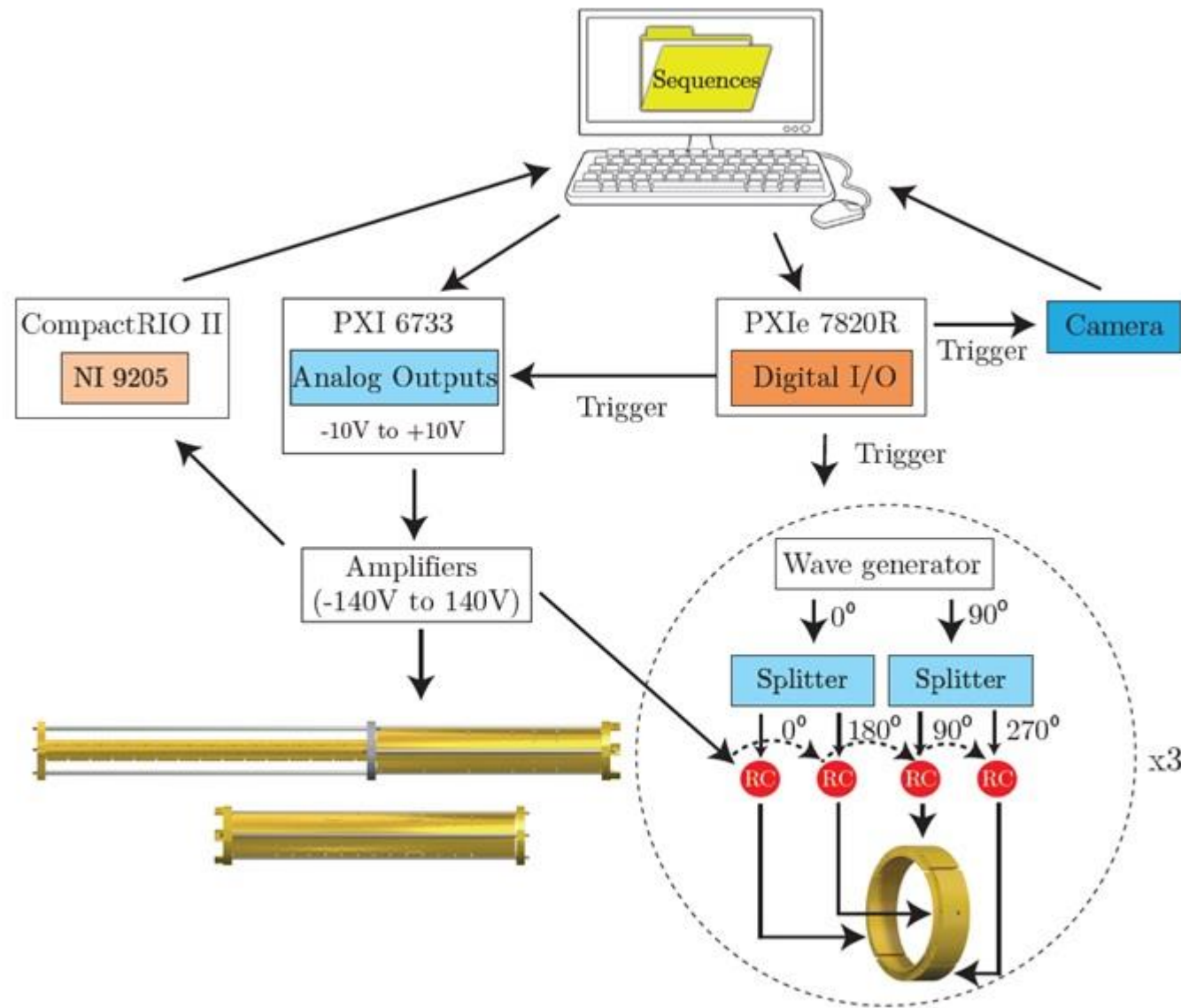
This is the photo of room temperature vacuum test. The conductance and volume of this vacuum system is close to the GBAR cold UHV vacuum pipe.

This chamber is not only for vacuum test, but also for electron test in room temperature. Trapping electron in MRE and observing by MCP is possible under 1×10^{-7} Torr in room temperature. For the electron test, we are preparing Electron Gun, Faraday Cup, MCP/PS.

Vacuum Test in Room Temperature



Vacuum Control System

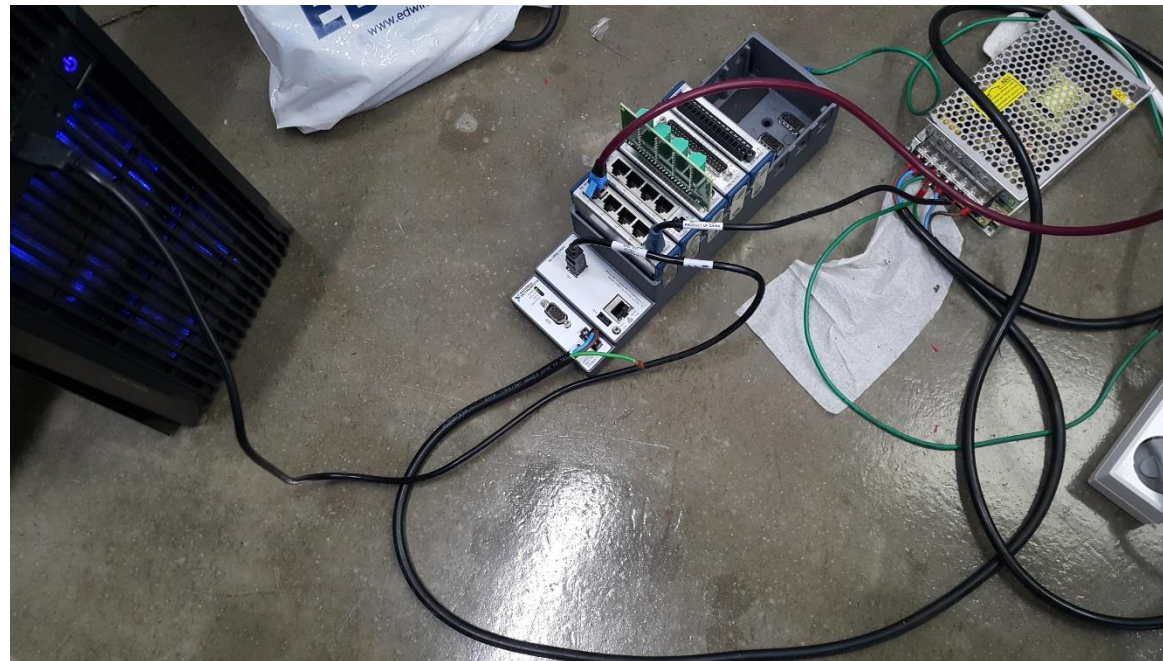
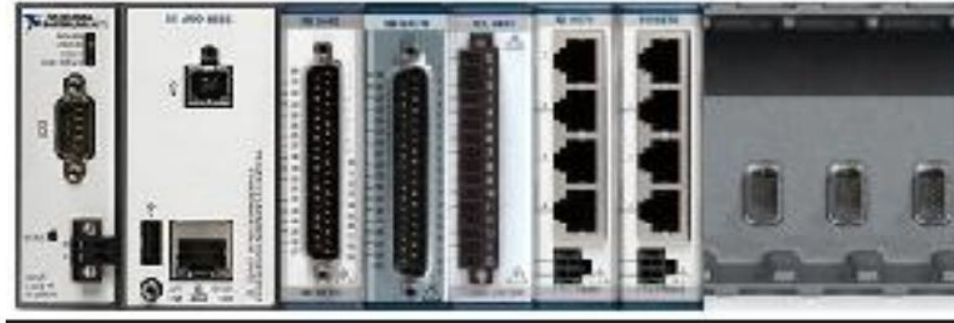


National Instrument's 'Compact RIO' system is used for control of vacuum system. Overall control system using 'PXIe' system is designed like this.

Vacuum Control System

NI CRIO

Configuration ID: [CR5457792](#)



MRE Control System

NI PXI System

Configuration ID: [PX5457782](#)



Thank You!